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Class	Subclass	ISSUE CLASSIFICATION

PATENT NUMBER

U.S. UTILITY Patent Application

O.I.P.E. SCANNED Q.A.	PATENT DATE

APPLICATION NO.	CONT/PRIOR	CLASS	SUBCLASS	ART UNIT	EXAMINER
09/883210	F	257	750	2815	Nguyen

APPLICANTS

Hiroyuki Nitta
Yoshiaki Fukuzumi
Yusuke Kohyama

[redacted]

TITLE

Semiconductor device having a wiring layer of damascene structure and method for manufacturing the same

PTO-2040
12/99

ISSUING CLASSIFICATION

ORIGINAL CLASS	ORIGINAL SUBCLASS	CROSS REFERENCE(S) CLASS	CROSS REFERENCE(S) SUBCLASS (ONE SUBCLASS PER BLOCK)

INTERNATIONAL CLASSIFICATION

☐ Continued on Issue Slip Inside File Jacket

☐ TERMINAL DISCLAIMER	DRAWINGS			CLAIMS ALLOWED	
	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims	Print Claim for O.G.
☐ The term of this patent subsequent to _____ (date) has been disclaimed.				NOTICE OF ALLOWANCE MAILED	
☐ The term of this patent shall not extend beyond the expiration date of U.S Patent. No. _____				ISSUE FEE	
				Amount Due	Date Paid
☐ The terminal ____months of this patent have been disclaimed.				ISSUE BATCH NUMBER	

(Assistant Examiner) (Date)

(Primary Examiner) (Date)

(Legal Instruments Examiner) (Date)

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